PDTC114T series

NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = open

Rev. 08 — 9 February 2006

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistors (RET) family.

Table 1: Product overview

Type number	Package	Package			
	Philips JEITA JEDEC				
PDTC114TE	SOT416	SC-75	-	PDTA114TE	
PDTC114TK	SOT346	SC-59A	TO-236	PDTA114TK	
PDTC114TM	SOT883	SC-101	-	PDTA114TM	
PDTC114TS[1]	SOT54	SC-43A	TO-92	PDTA114TS	
PDTC114TT	SOT23	-	TO-236AB	PDTA114TT	
PDTC114TU	SOT323	SC-70	-	PDTA114TU	

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 100 mA output current capability
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Digital applications
- Controlling IC inputs

- Cost-saving alternative for BC847 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ



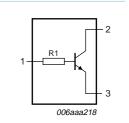
2. Pinning information

Table 3: Pinning

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	001aab347	1 R1 3 006aaa218

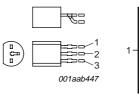
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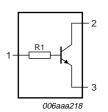
1	input (base)	
2	output (collector)	
3	GND (emitter)	001aab348



SOT54 variant

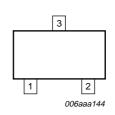
1	input (base)
2	output (collector)
3	GND (emitter)

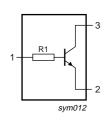




SOT23; SOT323; SOT346; SOT416

1	input (base)
2	GND (emitter)
3	output (collector)

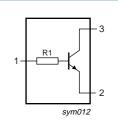




SOT883

1	input (base)
2	GND (emitter)
3	output (collector)





3. Ordering information

Table 4: Ordering information

Type number	Package					
	Name	Description	Version			
PDTC114TE	SC-75	plastic surface mounted package; 3 leads	SOT416			
PDTC114TK	SC-59A	plastic surface mounted package; 3 leads	SOT346			
PDTC114TM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTC114TS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
PDTC114TT	-	plastic surface mounted package; 3 leads	SOT23			
PDTC114TU	SC-70	plastic surface mounted package; 3 leads	SOT323			

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5: Marking codes

Type number	Marking code [1]
PDTC114TE	24
PDTC114TK	24
PDTC114TM	DT
PDTC114TS	TC114T
PDTC114TT	*12
PDTC114TU	*24

^{[1] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

5. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
Io	output current			-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C				
	SOT416		<u>[1]</u>	-	150	mW
	SOT346		<u>[1]</u>	-	250	mW
	SOT883		[2] [3]	-	250	mW
	SOT54		<u>[1]</u>	-	500	mW
	SOT23		<u>[1]</u>	-	250	mW
	SOT323		<u>[1]</u>	-	200	mW
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7: Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> -	-	833	K/W
	SOT346		<u>[1]</u> -	-	500	K/W
	SOT883		[2][3]	-	500	K/W
	SOT54		<u>[1]</u> _	-	250	K/W
	SOT23		<u>[1]</u> _	-	500	K/W
	SOT323		<u>[1]</u> -	-	625	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 60 μm copper strip line, standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

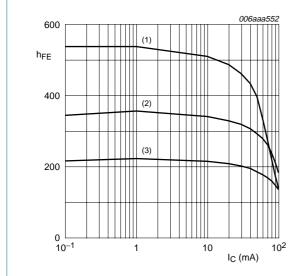
^[3] Device mounted on an FR4 PCB with $60~\mu m$ copper strip line, standard footprint.

7. Characteristics

Table 8: Characteristics

T_{amb} = 25 °C unless otherwise specified.

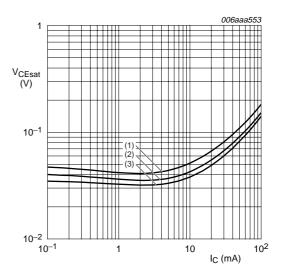
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
		$V_{CE} = 30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}$	200	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
R1	bias resistor 1 (input)		7	10	13	kΩ
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF





- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values

PDTC114T_SER_8

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8. Package outline

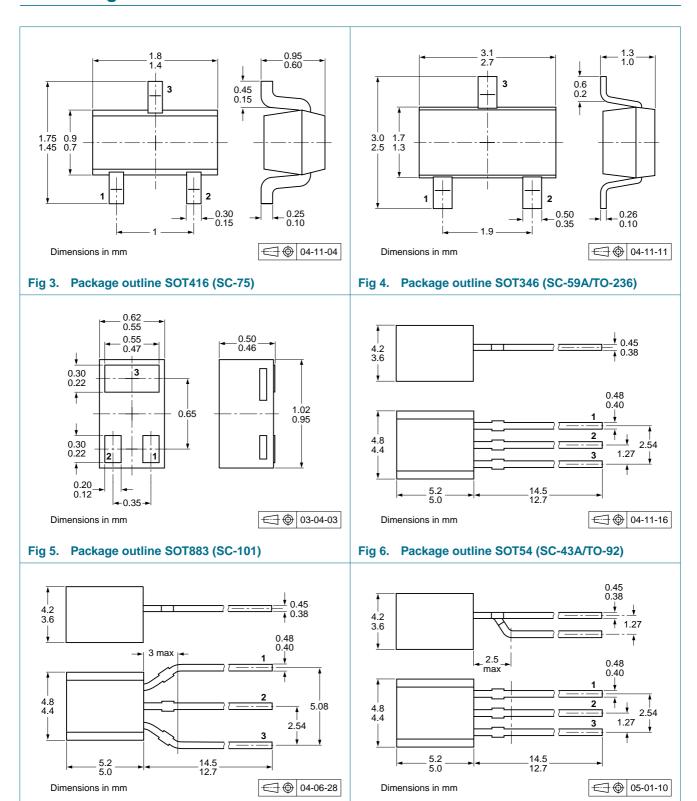
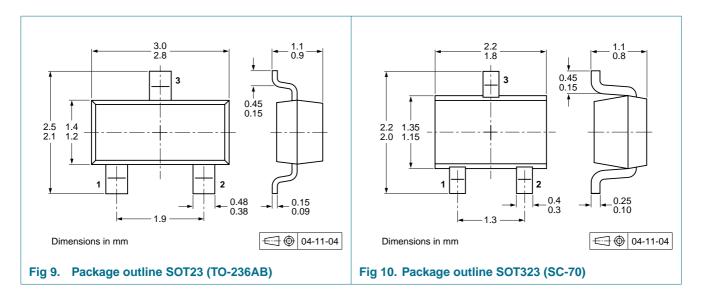


Fig 7. Package outline SOT54A

Fig 8. Package outline SOT54 variant



9. Packing information

Table 9: Packing methods
The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity		
			3000	5000	10000
PDTC114TE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC114TK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTC114TM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
PDTC114TS	SOT54	bulk, straight leads	-	-412	-
	SOT54A	tape and reel, wide pitch	-	-	-116
		tape ammopack, wide pitch	-	-	-126
	SOT54 variant	bulk, delta pinning	-	-112	-
PDTC114TT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
PDTC114TU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135

^[1] For further information and the availability of packing methods, see Section 15.

10. Revision history

Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PDTC114T_SER_8	20060209	Product data sheet	-	-	PDTC114T_SER_7
Modifications:	information Type number Table 1 "Profession 1.2" Section 1.3 Figure 1, 2, Figure 3, 4, Section 9 "Formation or support of the support o	of this data sheet has standard of Philips Se er PDTC114TEF remoduct overview": EIAJ "Features": amended "Applications": amended 5, 6, 9 and 10: superspacking information": a "Trademarks": added	emiconductors. byed in table header and ded seded by minimize	mended to JEITA	e new presentation and
PDTC114T_SER_7	20041011	Product specification	-	9397 750 14186	PDTC114T_SERIES_6
PDTC114T_SERIES_6	20040817	Product specification	-	9397 750 13664	PDTC114T_SERIES_5
PDTC114T_SERIES_5	20040119	Product specification	-	9397 750 11731	PDTC114T_SERIES_4
PDTC114T_SERIES_4	20030414	Product specification	-	9397 750 11011	PDTC114TE_2 PDTC114TK_2 PDTC114TS_2 PDTC114TT_3 PDTC114TU_3
PDTC114TU_3	19990416	Preliminary specification	-	9397 750 05599	PDTC114TU_2
PDTC114TU_2	19980519	Preliminary specification	-	9397 750 03908	PDTC114TU_1
PDTC114TU_1	19970716	Preliminary specification	-	9397 750 01149	-
PDTC114TT_3	19990416	Objective specification	-	9397 750 05598	PDTC114TT_2
PDTC114TT_2	19980519	Objective specification	-	9397 750 03912	PDTC114TT_1
PDTC114TT_1	19970714	Objective specification	-	9397 750 01371	-
PDTC114TS_2	19980518	Product specification	-	9397 750 03891	PDTC114TS_1
PDTC114TS_1	19970703	Product specification	-	9397 750 02297	-
PDTC114TK_2	19980519	Product specification	-	9397 750 03899	PDTC114TK_1

PDTC114T series

NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = open



Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PDTC114TK_1	19970528	Product specification	-	9397 750 01367	-
PDTC114TE_2	19980803	Product specification	-	9397 750 04123	PDTC114TE_1
PDTC114TE_1	19970711	Product specification	-	9397 750 02628	-



Level	Data sheet status [1]	Product status [2] [3]	Definition
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Philips Semiconductors

PDTC114T series

NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = open

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